## **LISTING OF THE CLAIMS**

1. (Currently Amended) A method of forming a liquid crystal display device comprising: forming a thin film transistor and a pixel electrode on a first substrate;

forming a dielectric frame having a first height and a sealant structure having a second height on a second substrate, the dielectric frame including a material having a small dielectric constant, the material including [[one of]] photoacrylate [[, polyimide and benzocyclobutene(BCB)]];

dispensing liquid crystal on the first substrate where the dielectric frame is not formed, wherein the dispensed liquid crystal moves and is uniformly distributed on the first substrate; and

attaching the first and second substrates to each other,

wherein the second height of the sealant structure is higher than the first height of the dielectric frame, a height difference between the first height and the second height is more than 1 µm, and the height difference between the sealant structure and dielectric frame allows the dispensed liquid crystal to be uniformly distributed on the first substrate.

- 2. (Previously Presented) The method of claim 1, wherein the sealant structure includes a material hardened by ultraviolet ray.
- 3. (Cancelled)
- 4. (Original) The method of claim 1, further comprising forming an electric field inducing window in the pixel electrode.
- 5. (Previously Amended) The method of claim 4, wherein the electric field inducing window has a slit shape.
- 6. (Withdrawn) The method of claim 1, wherein forming the thin film transistor includes: forming a gate electrode on the first substrate; forming a gate insulating film on the first substrate;

forming a semiconductor layer on the gate insulating film; and

forming source and drain electrodes on the semiconductor layer.

7. (Previously Presented) The method of claim 1, wherein the thin film transistor is formed to have an L-shaped channel.

- 8. (Withdrawn) The method of claim 1, wherein the thin film transistor is formed to have a U-shape.
- 9. (Original) The method of claim 1, wherein the dielectric frame drives the liquid crystal in various directions.
- 10-11. (Cancelled)
- 12. (Original) The method of claim 1, further comprising forming a common electrode on the second substrate.
- 13. (Original) The method of claim 12, wherein the dielectric frame is formed on the common electrode.
- 14. (Original) The method of claim 1, further comprising forming an alignment layer on at least one of the first and second substrates.
- 15. (Original) The method of claim 14, wherein the alignment layer is selected from the group consisting of polyimide, polyamide, polyvinyl alcohol, polyamic acid, and silicon oxide.
- 16. (Withdrawn) The method of claim 14, wherein the alignment layer is selected from the group consisting of polyvinylcinnamate, polysiloxanecinnamate, and cellulosecinnamate.
- 17. (Original) The method of claim 1, further comprising forming a phase difference film on at least one of the first and second substrates.
- 18. (Original) The method of claim 17, wherein the phase difference film includes a negative uniaxial film.

19. (Previously Presented) The method of claim 17, wherein the phase difference film includes a negative biaxial film.

- 20. (Original) The method of claim 1, wherein the first height is a range of 1-2  $\mu$ m and the second height is in a range of 5-8  $\mu$ m.
- 21. (Withdrawn) The method of claim 1, wherein the first height is a range of 1-2  $\mu$ m and the second height is about 4  $\mu$ m.
- 22. (Withdrawn) The method of claim 1, wherein the first height is a range of 1-1.5  $\mu$ m and the second height is about 3  $\mu$ m.
- 23. (Withdrawn) The method of claim 1, wherein the first height is about 1  $\mu$ m and the second height is about 2  $\mu$ m.
- 24. (Withdrawn) A method of forming a liquid crystal display device comprising:

forming a gate electrode on a first substrate;

forming a gate insulating film on the gate electrode and the first substrate;

forming a semiconductor layer on the gate insulating film;

forming source and drain electrodes on the semiconductor layer;

forming a pixel electrode contacting the drain electrode, the pixel electrode including an electric field inducing window;

forming a dielectric frame having a first height and a sealant having a second height on a second substrate, the first height of the dielectric frame being different from the second height of the sealant, the dielectric frame capable of causing an electric field distortion;

dispensing liquid crystal on the first substrate; and attaching the first and second substrates to each other.

25. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-2  $\mu$ m and the second height is in a range of 5-8  $\mu$ m.

26. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-2  $\mu$ m and the second height is about 4  $\mu$ m.

- 27. (Withdrawn) The method of claim 24, wherein the first height is a range of 1-1.5  $\mu m$  and the second height is about 3  $\mu m$ .
- 28. (Withdrawn) The method of claim 24, wherein the first height is about 1  $\mu m$  and the second height is about 2  $\mu m$ .
- 29. (Cancelled)